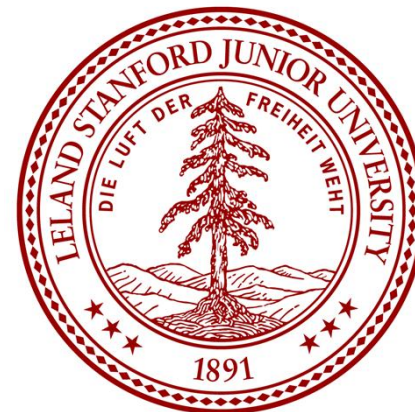


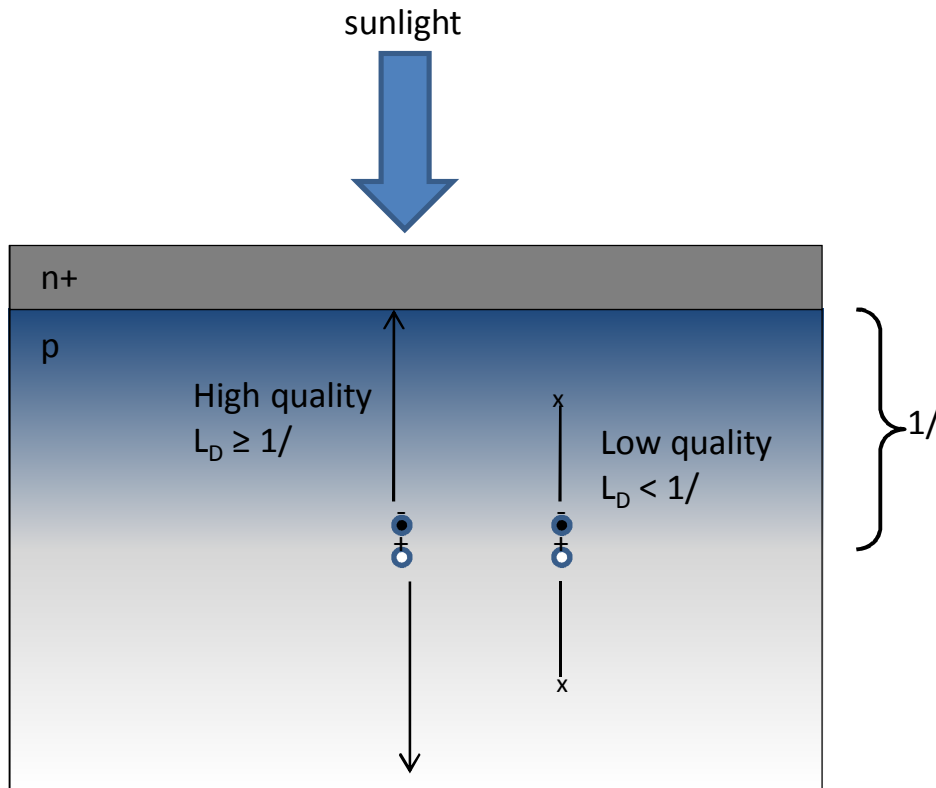
Comparison of Novel 3D Nanoarchitectures for Solar Cells

August 23, 2011

Artit Wangperawong, Carl Hagglund and Stacey F. Bent
Stanford University



Carrier collection in planar devices

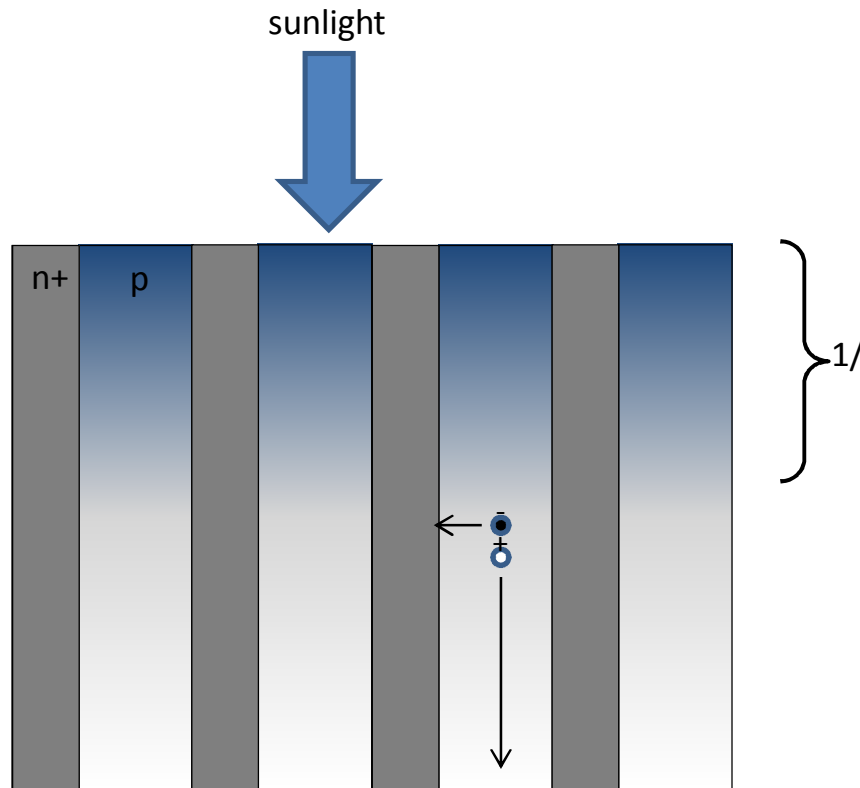


Diffusion length of minority carriers needs to be longer than the absorption depth for efficient carrier collection.

Problem: High quality materials are expensive. As for cheaper low quality materials, L_D is nanoscale.

Solution: Consider vertical nanojunctions to decouple absorption from collection.

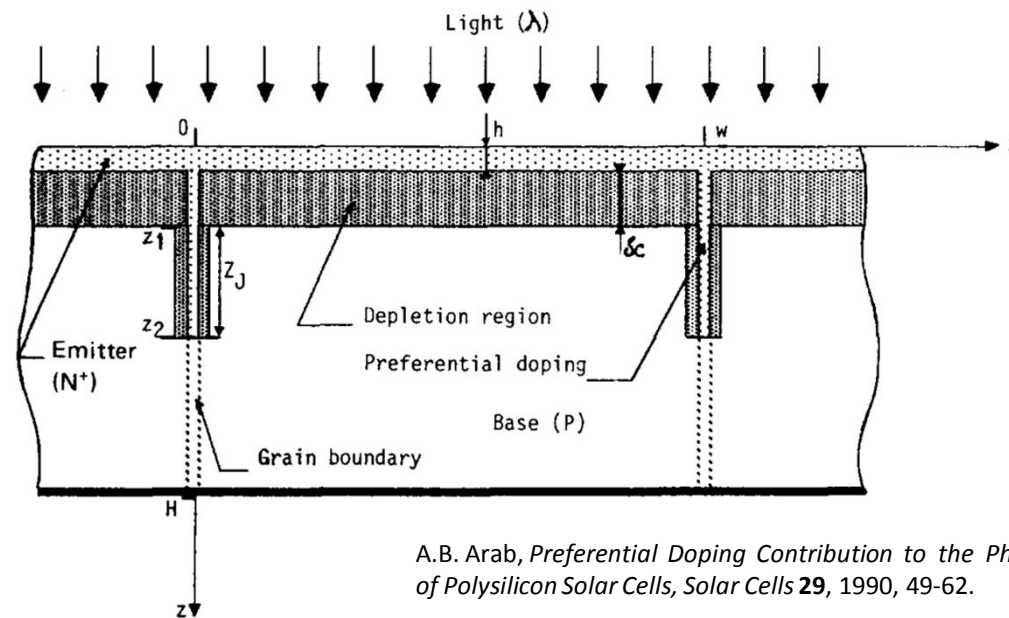
Carrier collection in vertical junctions



- " Diffusion length of minority carriers no longer needs to be greater than the absorption depth for efficient carrier collection.
- " Low-quality materials can be made more efficient.
- " Since L_D is nanoscale, junction spacing should be nanoscale.
- " To maximize benefit, we need to consider 3-D interdigitated nanojunctions.
- " 4 designs will be presented here.

Not a new idea - Vertical Nanojunctions from 1980s

1. Preferential doping along grain boundaries



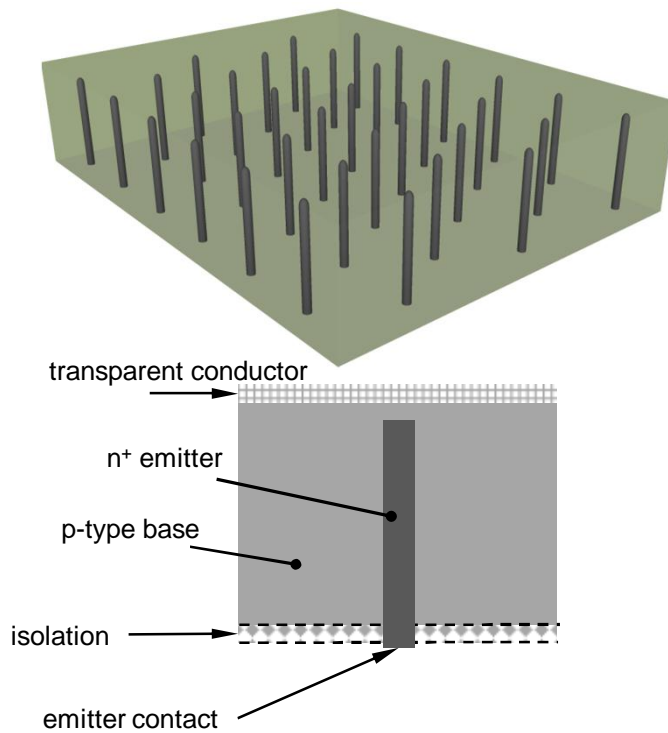
A.B. Arab, *Preferential Doping Contribution to the Photoresponse of Polysilicon Solar Cells*, *Solar Cells* **29**, 1990, 49-62.

This effect has also been reported for CIGS and CdTe

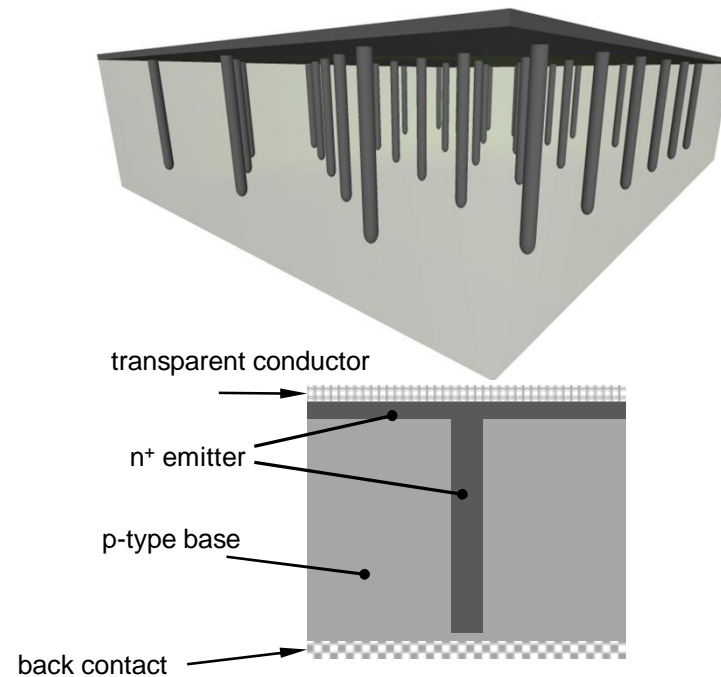
New 3D interdigitated designs reported

Note that electronic communication between junctions

2. Point-contact nanojunctions



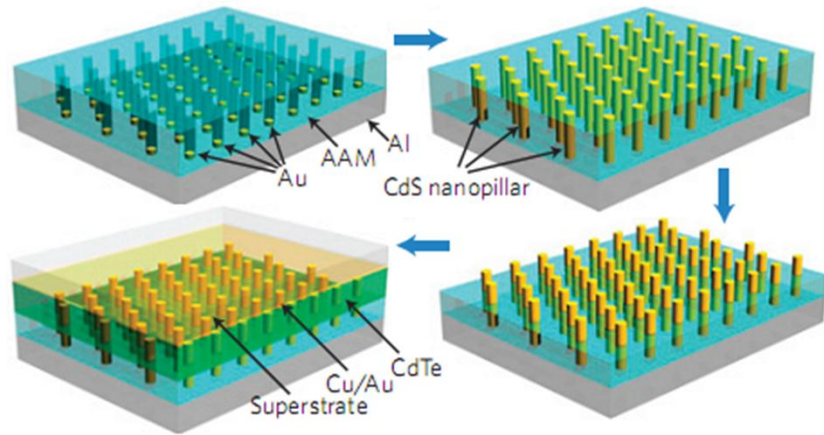
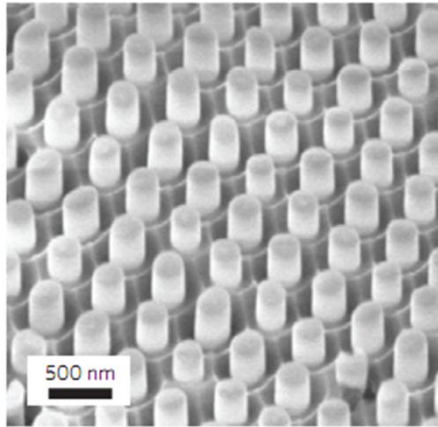
3. Extended nanojunctions



A. Wangperawong, S.F. Bent, *Appl. Phys. Lett.* **98**, 233106 (2011).

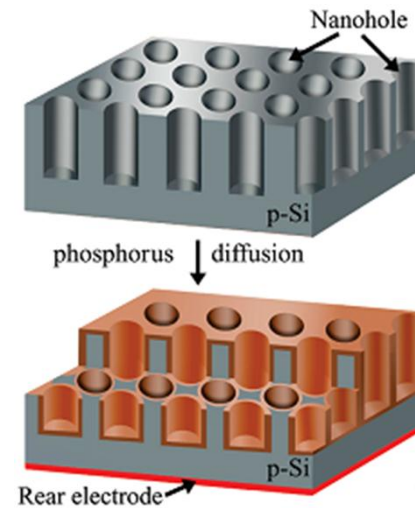
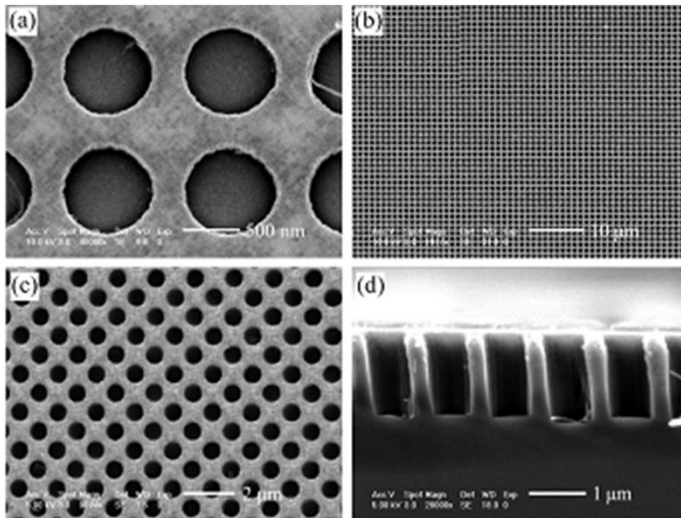
Experimental interdigitated devices

2. Point-contact nanojunctions



Fan, et al., *Nature Mater.* 8, 648 (2009).

3. Extended nanojunctions

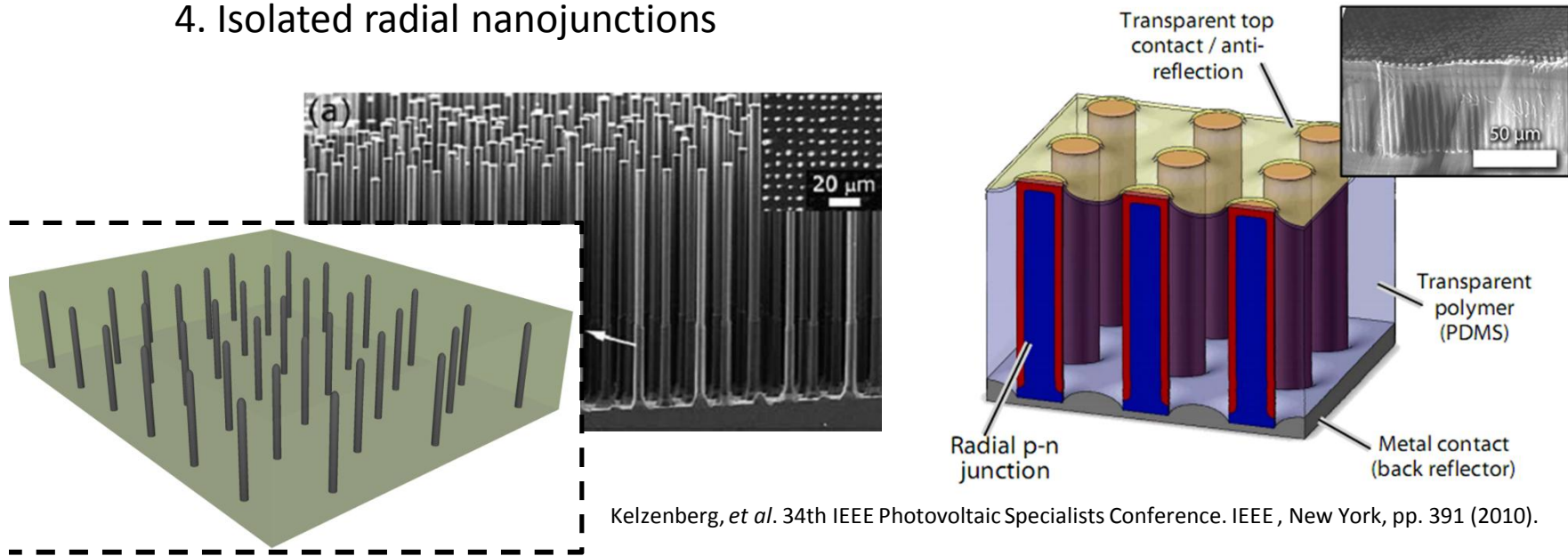


Peng, et al., *J. Am. Chem. Soc.*, 132 (20), 6872 (2010).

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Modeling beyond isolated nanojunctions

4. Isolated radial nanojunctions

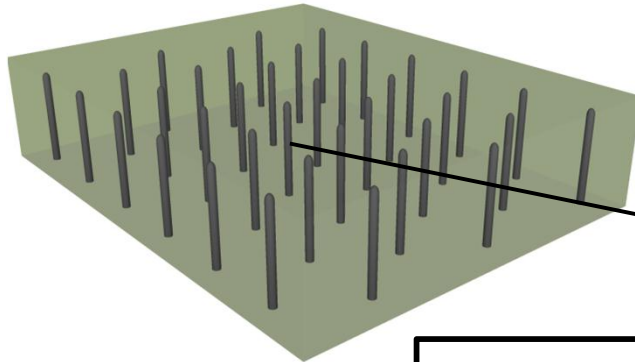


Limited 3D modeling work reported thus far

- “ Only on isolated radial junctions, i.e. nanowires.
- “ Interdigitated design \neq isolated radial junctions.
- “ Should consider 3D carrier collection – computationally expensive if numerical
- “ Is nano better than planar? Which nano is the best?
 - “ Depletion region lifetime greater than bulk lifetime + operate in full depletion
 - “ Not likely, not generally applicable

Modeling Approach

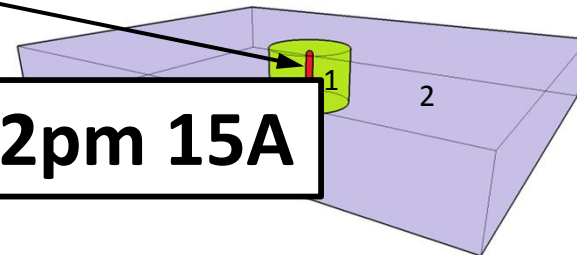
1. Point-contact nanojunctions



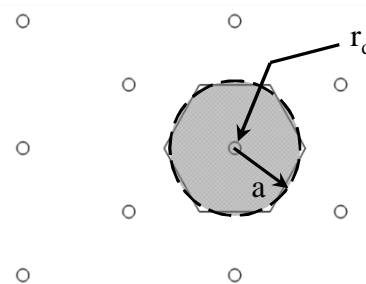
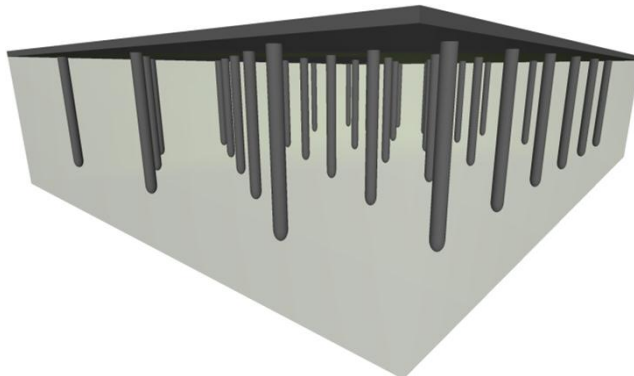
Analytical approach using effective medium approximation to solve diffusion-collection problem in 3-D:

$$\frac{1}{r} \frac{\partial}{\partial r} \left(r \frac{\partial \varphi_m}{\partial r} \right) + \frac{\partial^2 \varphi_m}{\partial z^2} - \frac{1}{L_m^2} \varphi_m = 0 \quad m=1,2$$

More details 2pm 15A



2. Extended nanojunctions



Boundary conditions due to continuity:

$$\varphi_1(r=a, z) = \varphi_2(r=a, z)$$

$$\left. \frac{\partial \varphi_1}{\partial r} \right|_{r=a} = \left. \frac{\partial \varphi_2}{\partial r} \right|_{r=a}$$

CdTe/CdS devices, high vs. low

Property	High	Low
Acceptor doping, N_a (cm ⁻³)	2×10^{14}	1×10^{17}
Electron mobility, μ_n (cm ² /Vs)	320	100
Electron lifetime, τ_n (ns)	1	1×10^{-2}
Diffusion length, L_n (μ m)	0.910	0.050

higher doping

lower mobility

lower lifetime

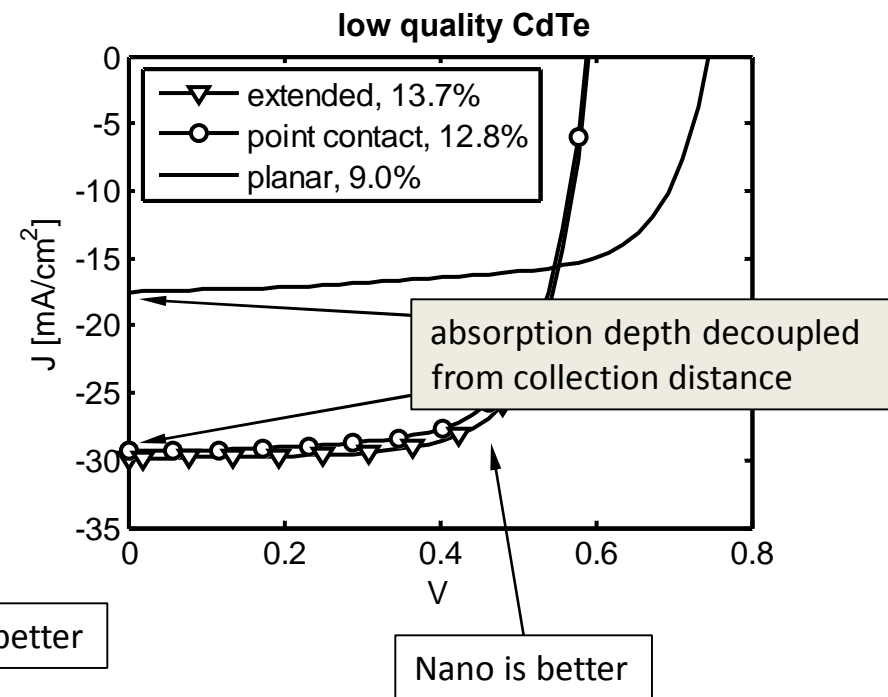
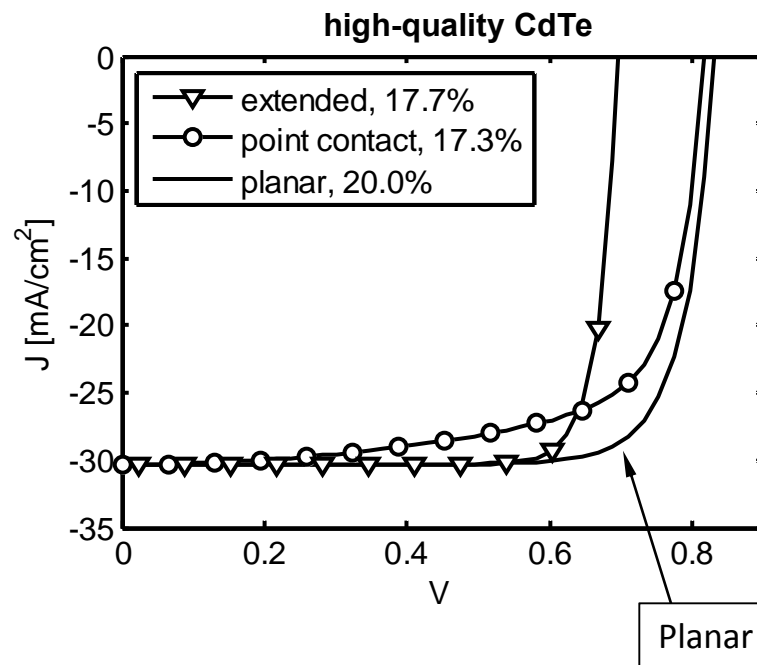
lower diffusion length

~ Z. Fan, *et al.*, *Nature Mater.* 8, 648 (2009).

~ R. Kapadia, *et al.*, *Appl. Phys. Lett.* 96, 103116 (2010).

~ S. Adachi, *Properties of Group-IV, III-V and II-VI Semiconductors*, Wiley, West Sussex, England (2005).

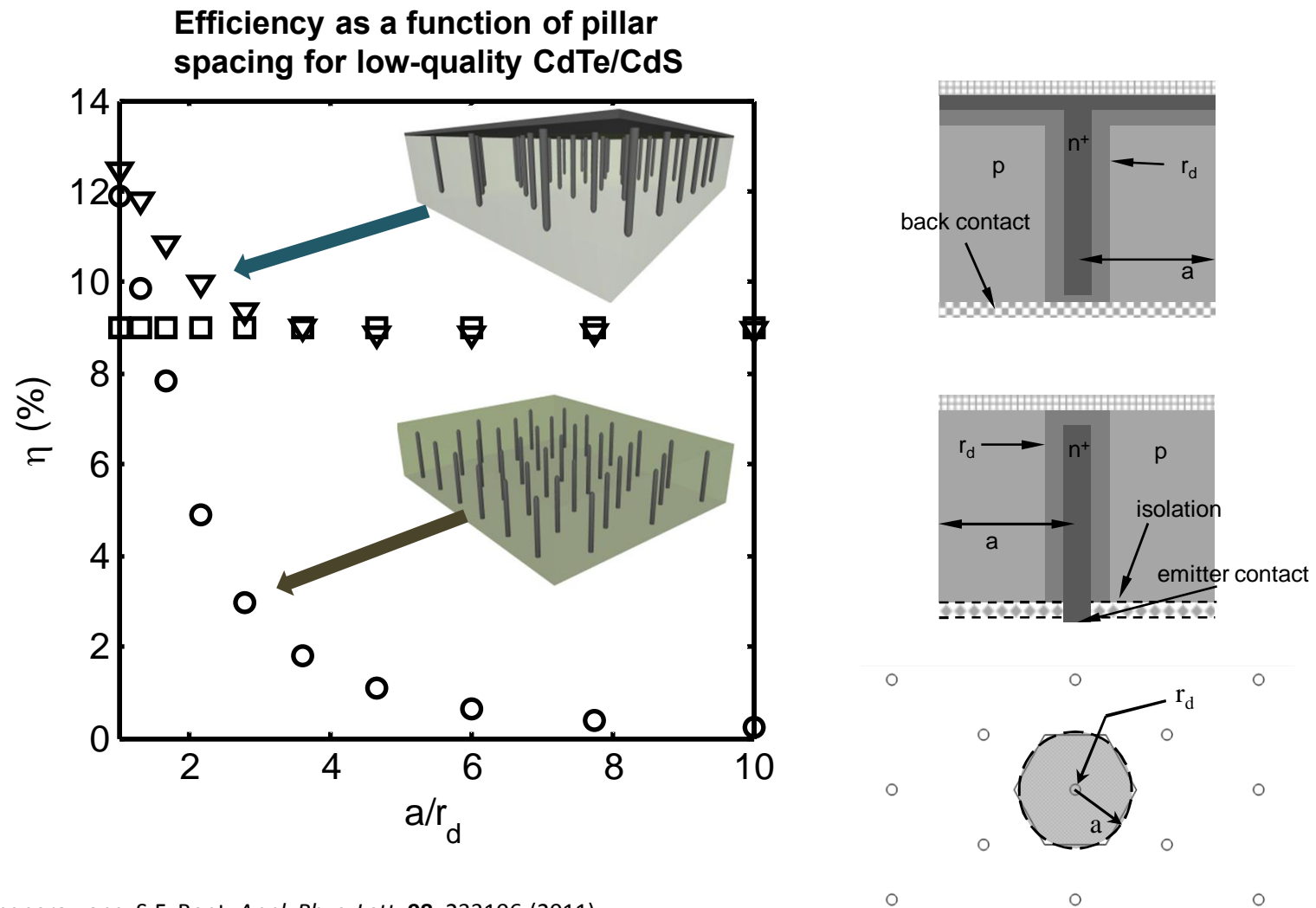
~ M. Gleockler, *et al.*, Numerical modeling of CIGS and CdTe solar cells: setting the baseline, *Proc. World Conf. Photov. Energy Conv.*, 3, 491 (2004).



A. Wangperawong, S.F. Bent, *Appl. Phys. Lett.* **98**, 233106 (2011).

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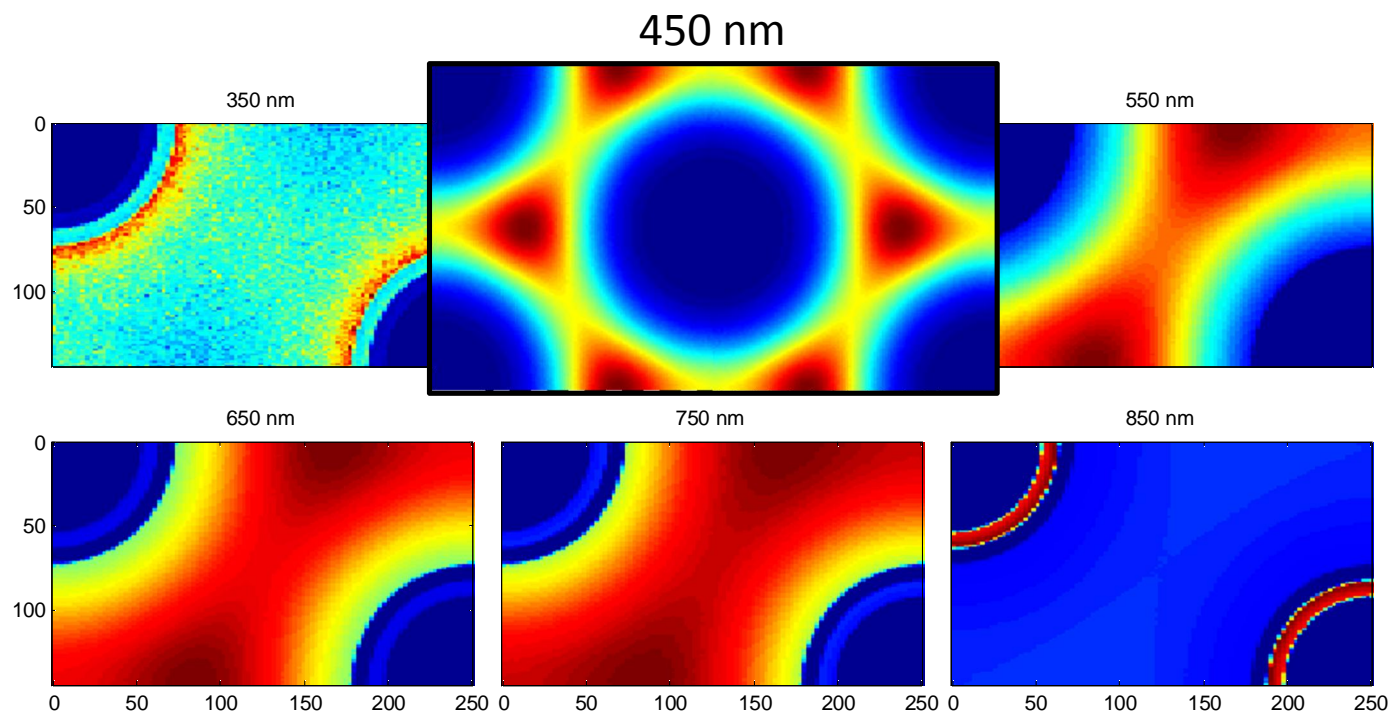
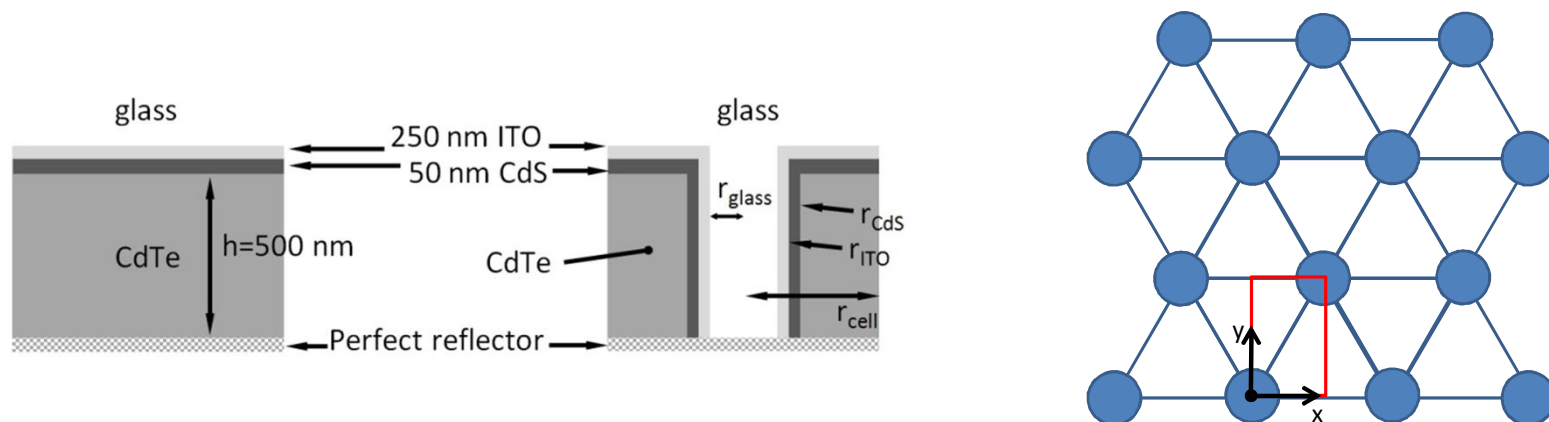
Extended device most robust



A. Wangperawong, S.F. Bent, *Appl. Phys. Lett.* **98**, 233106 (2011).

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Absorption in CdTe/CdS/ITO/SLG



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Conclusion

- We developed an analytical model for
 - diffusion in 3-D, interdigitated nanojunctions
 - both point-contact and extended architectures
 - any system involving diffusion, e.g. PEC, PV, etc.
- Nanojunctions can
 - decouple absorption depth from collection distance
 - improve performance of low quality PV absorbers, making use of inexpensive materials
- Modeling valuable for choosing the right nano-architecture
 - the efficiency of the extended nanojunction geometry is superior to other designs considered
 - point-contact nanojunction, isolated radial nanojunction, planar
- Various geometries and materials systems can be further explored
 - there could be an even better design out there

Acknowledgements



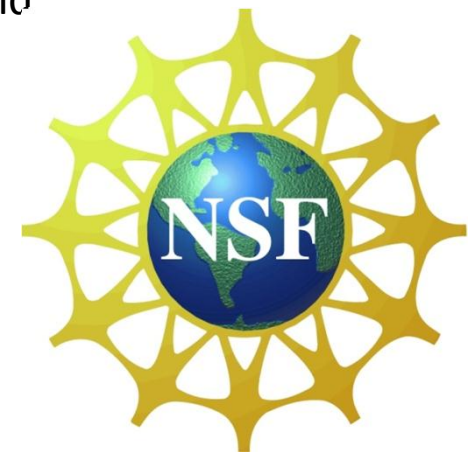
cneec.stanford.edu

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Questions?